FAIRCHILD SEMICONDUCTOR®

June 2003

FDS6990A

Dual N-Channel Logic Level PowerTrench™ MOSFET

General Description

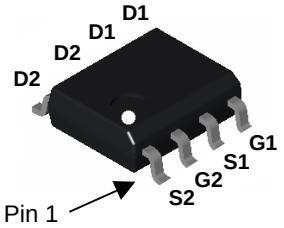
These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

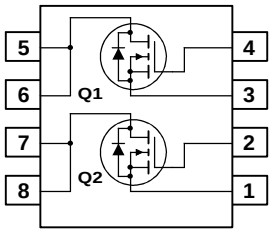
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 7.5 A, 30 V. $R_{DS(ON)}$ = 18 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 23 mΩ @ V_{GS} = 4.5 V
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability

SO-8





Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Drain Current – Continuous	(Note 1a)	7.5	A
	– Pulsed		20	
P_D	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	1.0	
		(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6990A	FDS6990A	13"	12mm	2500 units

©2003 Fairchild Semiconductor Corporation

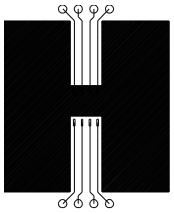
Electrical Characteristics

T_A = 25°C unless otherwise noted

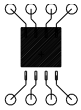
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		26		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55°C			1 10	µA
I_{GSS}	Gate–Source Leakage	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		–4		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 10 V, I_D = 7.5 A V_{GS} = 4.5 V, I_D = 6.5 A V_{GS} = 10 V, I_D = 7.5 A, T_J = 125°C		11 13 15	18 23 31	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = 10 V, V_{DS} = 5 V	20			A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 7.5 A		33		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		1235		pF
C_{oss}	Output Capacitance			295		pF
C_{rss}	Reverse Transfer Capacitance			120		pF
R_G	Gate Resistance	V_{GS} = 15 mV, f = 1.0 MHz		2.3		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 15 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		10	19	ns
t_r	Turn–On Rise Time			5	10	ns
$t_{d(off)}$	Turn–Off Delay Time			28	44	ns
t_f	Turn–Off Fall Time			10	19	ns
Q_g	Total Gate Charge	V_{DS} = 15 V, I_D = 7.5 A, V_{GS} = 5 V		12	17	nC
Q_{gs}	Gate–Source Charge			3.5		nC
Q_{gd}	Gate–Drain Charge			4.2		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				1.3	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.3 A (Note 2)		0.7	1.2	V
t_{rr}	Diode Reverse Recovery Time	I_F = 7.5 A, d_{iF}/d_t = 100 A/µs		24		nS
Q_{rr}	Diode Reverse Recovery Charge			13		nC

Notes:

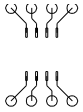
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5in^2 pad of 2 oz copper



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz copper



c) 135°C/W when mounted on a minimum mounting pad.

Scale 1 : 1 on letter size paper

Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

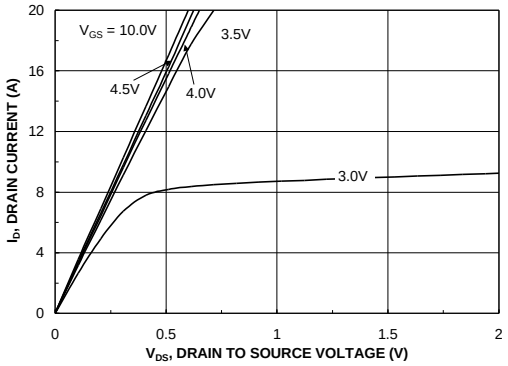


Figure 1. On-Region Characteristics.

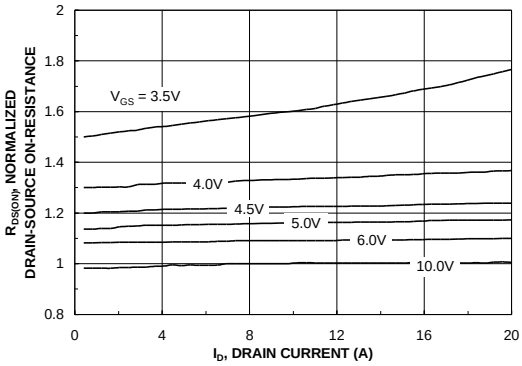


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

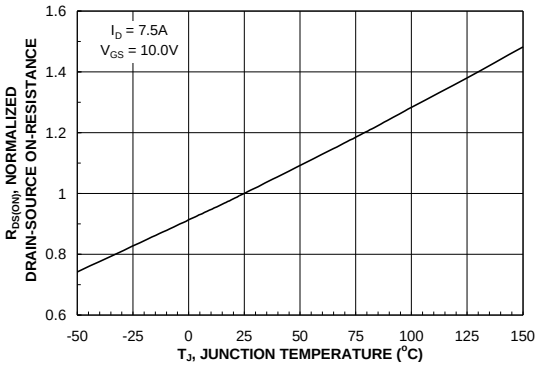


Figure 3. On-Resistance Variation with Temperature.

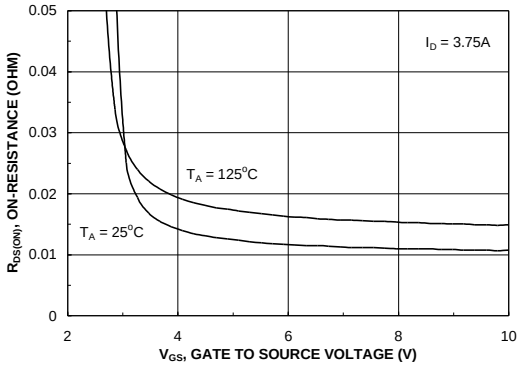


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

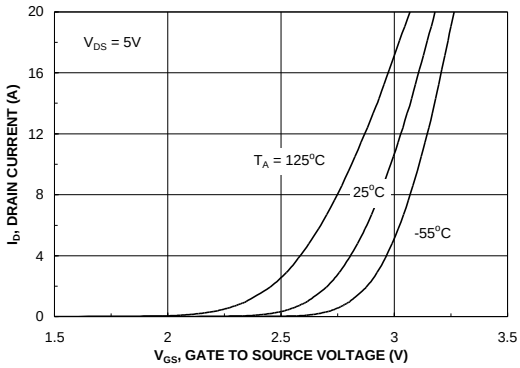


Figure 5. Transfer Characteristics.

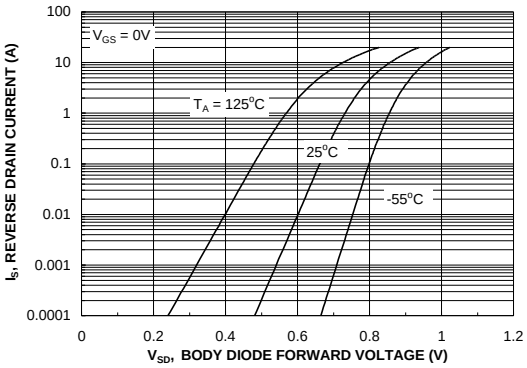


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

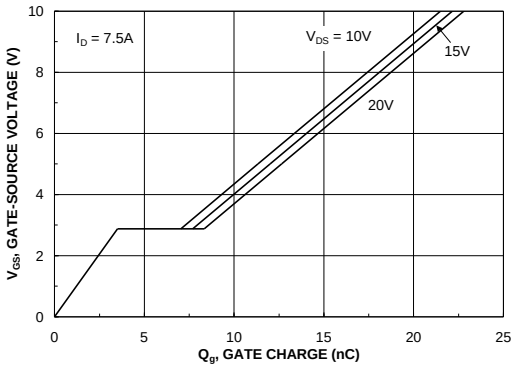


Figure 7. Gate Charge Characteristics.

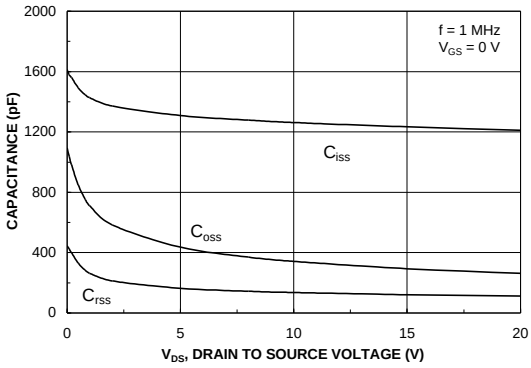


Figure 8. Capacitance Characteristics.

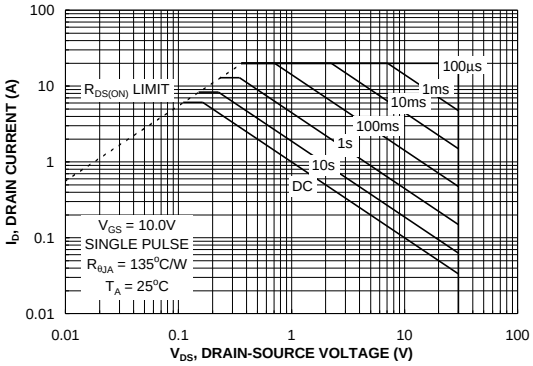


Figure 9. Maximum Safe Operating Area.

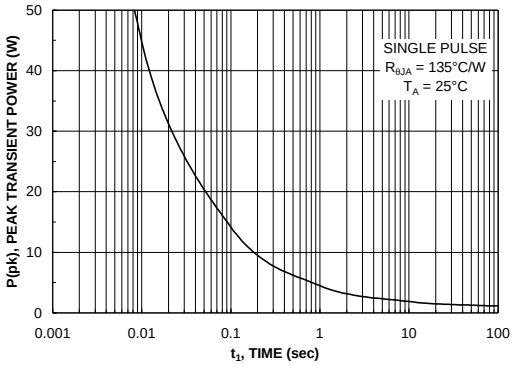


Figure 10. Single Pulse Maximum Power Dissipation.

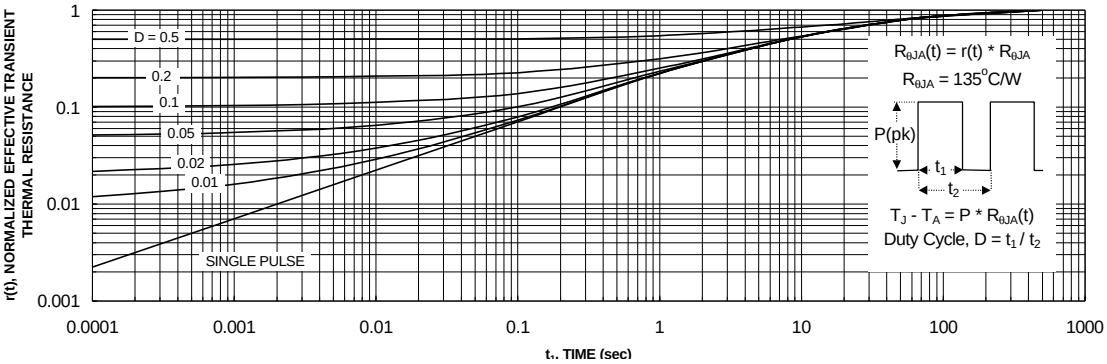


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™
ActiveArray™
Bottomless™
CoolFET™
CROSSVOLT™
DOME™
EcoSPARK™
E^2CMOS™
EnSigna™
FACT™
FACT Quiet Series™
FAST®
FASTr™
FRFET™
GlobalOptoisolator™
GTO™
HiSeC™
I^2C™
ImpliedDisconnect™
ISOPLANAR™
LittleFET™
MICROCOUPLER™
MicroFET™
MicroPak™
MICROWIRE™
MSX™
MSXPro™
OCX™
OCXPro™
OPTOLOGIC®
OPTOPLANAR™
PACMAN™
POP™
Power247™
PowerTrench®
QFET®
QS™
QT Optoelectronics™
Quiet Series™
RapidConfigure™
RapidConnect™
SILENT SWITCHER®
SMART START™
SPM™
Stealth™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SyncFET™
TinyLogic®
TINYOPTO™
TruTranslation™
UHC™
UltraFET®
VCX™
Across the board. Around the world.™
The Power Franchise™
Programmable Active Droop™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.
As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

О компании

ООО "ТрейдЭлектроникс" - это оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов. Реализуемая нашей компанией продукция насчитывает более полумиллиона наименований.

Благодаря этому наша компания предлагает к поставке практически не ограниченный ассортимент компонентов как оптовыми, мелкооптовыми партиями, так и в розницу.

Наличие собственной эффективной системы логистики обеспечивает надежную поставку продукции по конкурентным ценам в точно указанные сроки.

Срок поставки со стоков в **Европе и Америке – от 3 до 14 дней.**

Срок поставки из **Азии – от 10 дней.**

Благодаря развитой сети поставщиков, помогаем в поиске и приобретении экзотичных или снятых с производства компонентов.

Предоставляем спец цены на элементы для создания инженерных сэмплов.

Упорный труд, качественный результат дают нам право быть уверенными в себе и надежными для наших клиентов.

Наша компания это:

- Гарантия качества поставляемой продукции
- Широкий ассортимент
- Минимальные сроки поставок
- Техническая поддержка
- Подбор комплектации
- Индивидуальный подход
- Гибкое ценообразование

Наша организация особенно сильна в поставках модулей, микросхем, пассивных компонентов, ксайленсах (XC), EPF, EPM и силовой электроники.

Большой выбор предлагаемой продукции, различные виды оплаты и доставки, позволят Вам сэкономить время и получить максимум выгоды от сотрудничества с нами!

Trade Electronics.ru

гарантия бесперебойности производства и качества выпускаемой продукции

Перечень производителей, продукцию которых мы поставляем на российский рынок

AMD
ANALOG DEVICES
BOURNS
Coilcraft
élantec Semiconductor, Inc.
HARRIS
Infineon
JRC
MICREL
MOTOROLA
nichicon
PHILIPS
ROHM
SGS-THOMSON
Sipex
TAIYO YUDEN
TOKO
ZILOG
Winbond
Allegro
ATMEL
BURR - BROWN
EXAR
HITACHI
intel
Lattice
muRata
OKI
QUALCOMM
SAMSUNG
SHARP
SONY
TDK
TOSHIBA
KYOCERA
ALTERA
AVX
CITILYST
CYPRESS
FAIRCHILD SEMICONDUCTOR
HOLTEK
International IOR Rectifier
LINEAR TECHNOLOGY
MITSUBISHI
National Semiconductor
ON Semiconductor
REALTEK
SANYO
SHINDENGEN
SGS
TECCOR
TUNDRA
XILINX
Amphenol
Bay Linear
CIRRUS LOGIC
DALLAS
FUJITSU
IDT
intersil
MAXIM
molex
NEC
Panasonic
RENESAS
SII
SIEMENS
ST
Texas Instruments
VISHAY
ZETEX SEMICONDUCTORS

Trade Electronics.ru

гарантия бесперебойности производства и качества выпускаемой продукции

С удовольствием будем прорабатывать для Вас поставки всех необходимых компонентов по текущим запросам для скорейшего выявления групп элементов, по которым сотрудничество именно с нашей компанией будет для Вас максимально выгодным!

С уважением,

Менеджер отдела продаж ООО

«Трейд Электроникс»

Шишлаков Евгений

8 (495)668-30-28 доб 169

manager28@tradeelectronics.ru

http://www.tradeelectronics.ru/